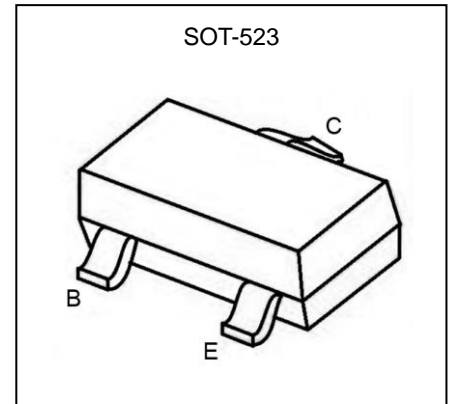




**MMBT3906T Transistor(PNP)**

**Feature**

- Epitaxial Planar Die Construction
- Complementary NPN Type Available(MMBT3904)
- Ideal for Medium Power Amplification and Switching



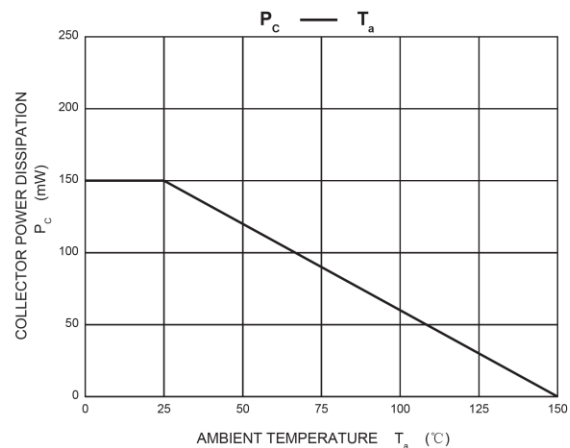
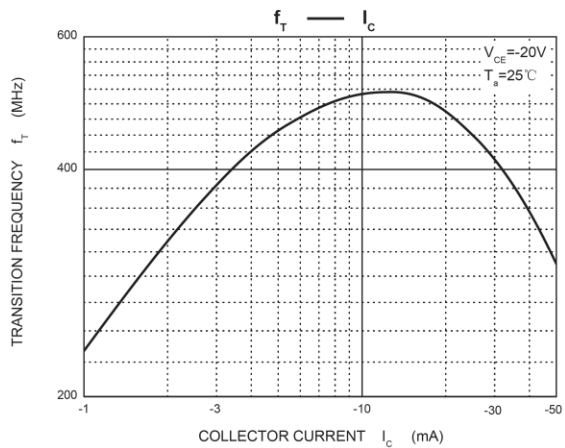
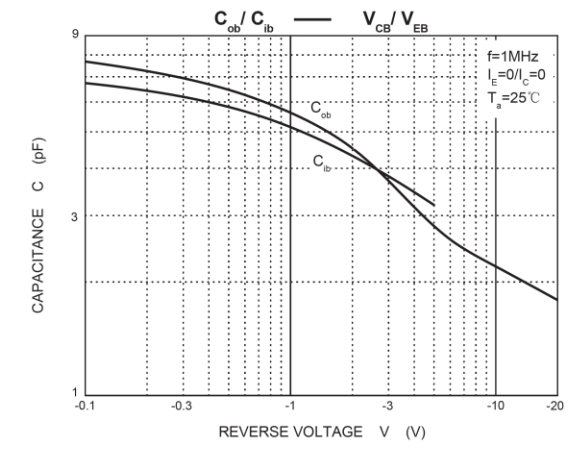
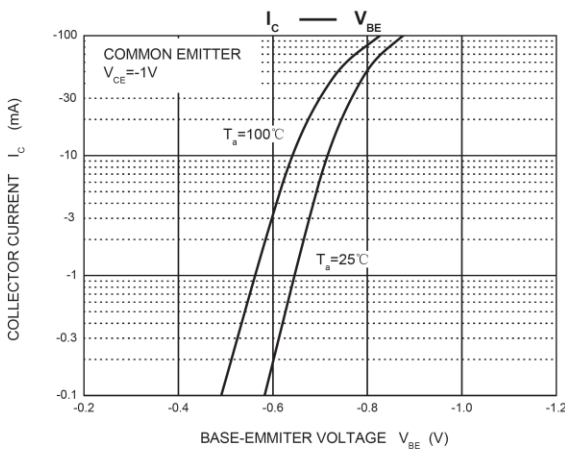
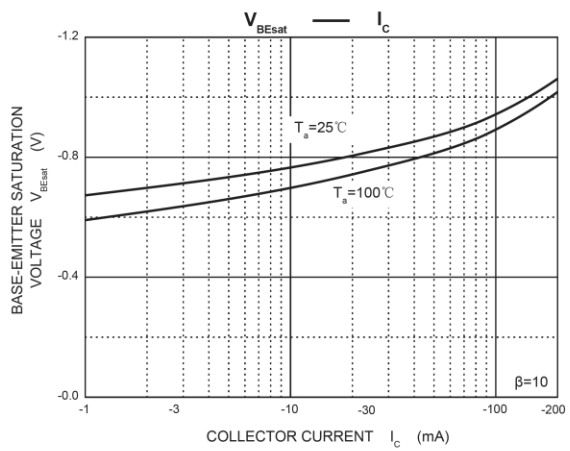
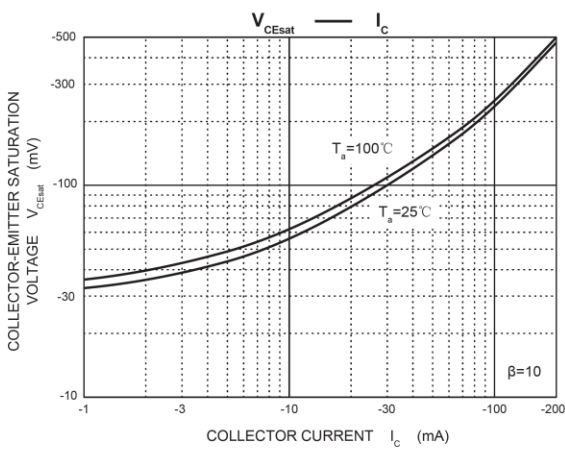
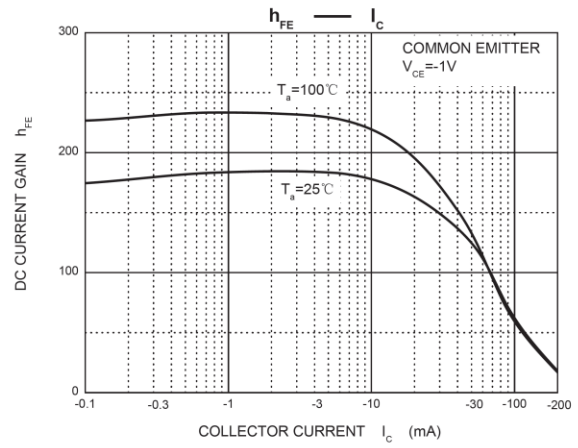
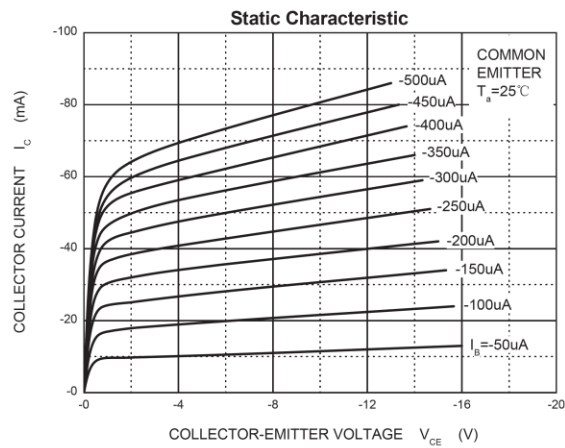
**MAXIMUM RATINGS (T<sub>a</sub>=25°C unless otherwise noted)**

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CB0</sub>	-40	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-40	V
Emitter-Base Voltage	V <sub>EBO</sub>	-5	V
Collector Current -Continuous	I <sub>c</sub>	-0.1	A
Power Dissipation	P <sub>d</sub>	0.15	W
Junction Temperature	T <sub>J</sub>	125	°C
Storage Temperature	T <sub>STG</sub>	-45~ +150	°C

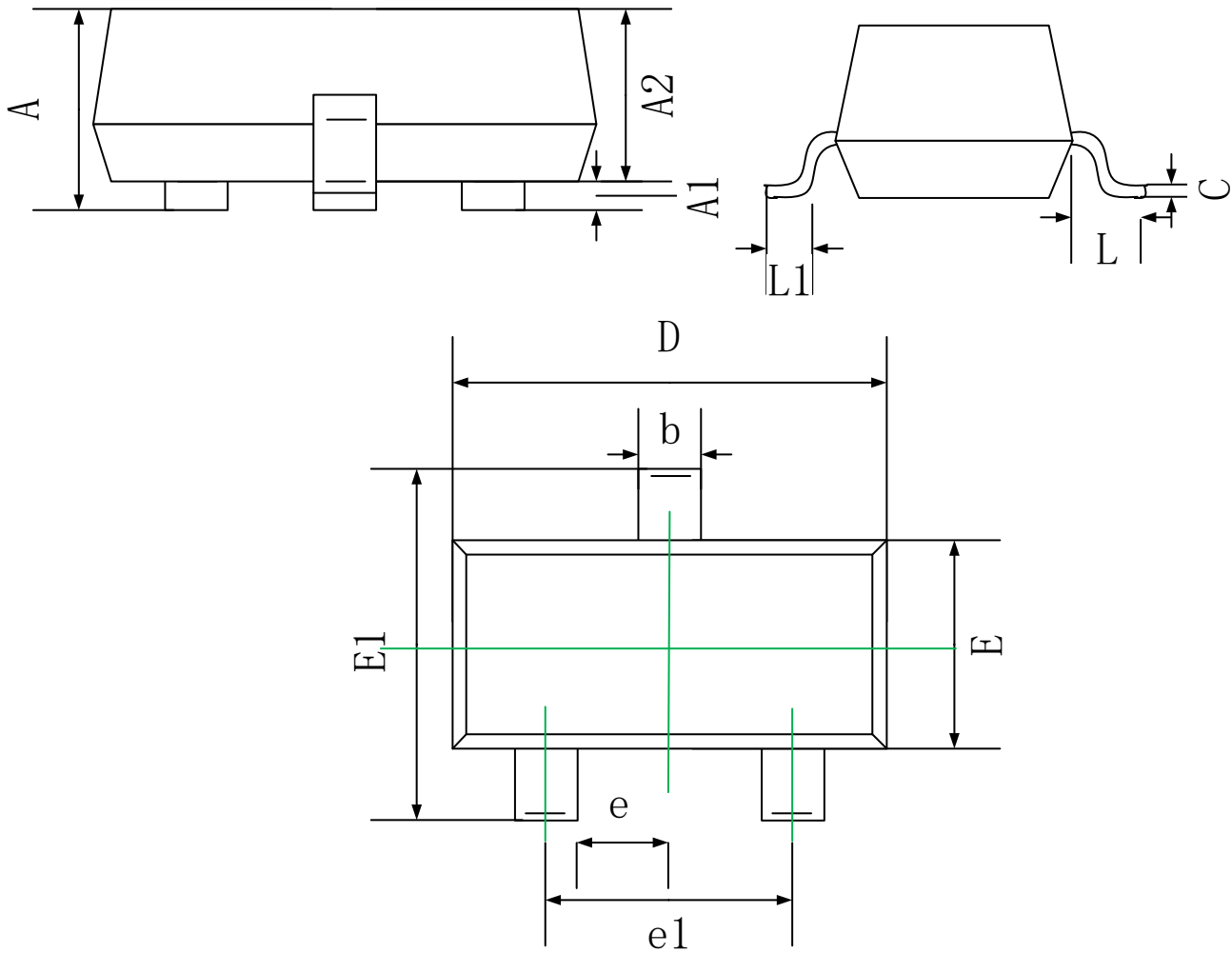
**ELECTRICAL CHARACTERISTICS(T<sub>a</sub>=25°C unless otherwise noted)**

Parameter	Symbol	Test Condition	Min	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>c</sub> =-10μA, I <sub>E</sub> =0	-40		V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>c</sub> =-1mA, I <sub>B</sub> =0	-40		V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =-10μA, I <sub>C</sub> =0	-5		V
Collector cut-off current	I <sub>CB0</sub>	V <sub>CB</sub> =-40V, I <sub>E</sub> =0		-100	nA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>CE</sub> =-5V, I <sub>C</sub> =0		-100	nA
Collector cut-off current	I <sub>CEX</sub>	V <sub>CE</sub> =-30V, V <sub>EB(OFF)</sub> =-3V		-200	nA
DC current gain	h <sub>FE</sub>	V <sub>CE</sub> =-1V, I <sub>C</sub> =-0.1mA	60		
		V <sub>CE</sub> =-1V, I <sub>C</sub> =-1mA	80		
		V <sub>CE</sub> =-1V, I <sub>C</sub> =-10mA	100	300	
		V <sub>CE</sub> =-1V, I <sub>C</sub> =-50mA	60		
		V <sub>CE</sub> =-1V, I <sub>C</sub> =-100mA	30		
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =-10mA, I <sub>B</sub> = -1mA		-0.25	V
		I <sub>C</sub> =-50mA, I <sub>B</sub> = -5mA		-0.4	V
Base-emitter saturation voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =-10mA, I <sub>B</sub> = -1mA	-0.65	-0.85	V
		I <sub>C</sub> =-50mA, I <sub>B</sub> = -5mA		-0.95	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> = -20V, I <sub>C</sub> =-10mA, f=100MHz	250		MHZ

Typical Characteristics



## SOT-523 Package Information



Symbol	Dimensions In Millimeters	
	Min	Max
A	0.700	0.900
A1	0.000	0.100
A2	0.700	0.800
b	0.150	0.250
c	0.100	0.200
D	1.500	1.700
E	0.700	0.900
E1	1.450	1.750
e	0.500 TYP	
e1	1.800	2.000
L	0.400 REF	
L1	0.260	0.460
$\theta$	0°	8°

单击下面可查看定价，库存，交付和生命周期等信息

[>>GP\(格瑞宝\)](#)